

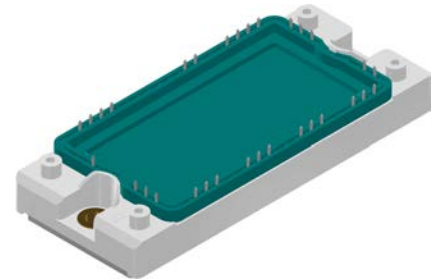
Standard Rectifier Module

3~ Rectifier
$V_{RRM} = 1600\text{ V}$
$I_{DAV} = 360\text{ A}$
$I_{FSM} = 1900\text{ A}$

3~ Rectifier Bridge + Softstart-Thyristor

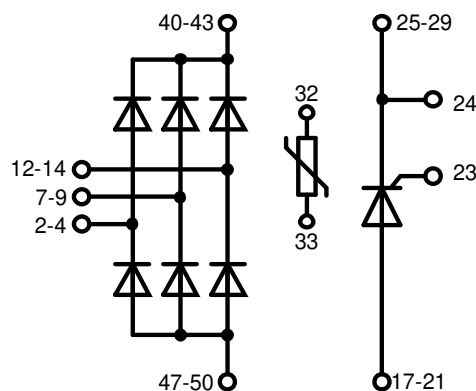
Part number

MDMA360UC1600TED



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification plus Softstart-Thyristor
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: E2-Pack

- Isolation Voltage: 4300 V~
- Industry standard outline
- RoHS compliant
- PressFit-Pins for PCB mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

Disclaimer Notice

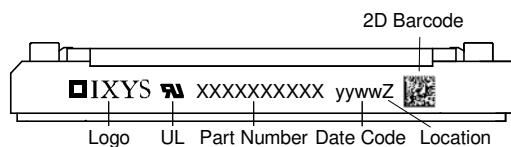
Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.



Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1700	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1600	V
I_R	reverse current	$V_R = 1600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	μA
		$V_R = 1600\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			3	mA
V_F	forward voltage drop	$I_F = 120\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1,25	V
		$I_F = 360\text{ A}$				1,80	V
		$I_F = 120\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1,23	V
		$I_F = 360\text{ A}$				1,98	V
I_{DAV}	bridge output current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 150^{\circ}\text{C}$			360	A
		rectangular $d = \frac{1}{3}$					
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0,82	V
r_F	slope resistance					3,4	m Ω
R_{thJC}	thermal resistance junction to case					0,25	K/W
R_{thCH}	thermal resistance case to heatsink				0,1		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				500	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			1,90	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			2,05	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			1,62	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1,75	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			18,1	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			17,5	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			13,0	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			12,7	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			10		pF

Softstart-Thyristor				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1600	V
I_{RD}	reverse current, drain current	$V_{RD} = 1600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	μA
		$V_{RD} = 1600\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			15	mA
V_T	forward voltage drop	$I_T = 150\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.34	V
		$I_T = 300\text{ A}$				1.73	V
		$I_T = 150\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.31	V
		$I_T = 300\text{ A}$				1.77	V
I_{TAV}	average forward current	$T_C = 90^{\circ}\text{C}$ 180° sine	$T_{VJ} = 150^{\circ}\text{C}$			150	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}\text{C}$			0.84	V
r_T	slope resistance					3.1	m Ω
R_{thJC}	thermal resistance junction to case					0.17	K/W
R_{thCH}	thermal resistance case to heatsink				0.080		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				735	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			2.40	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			2.59	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			2.04	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			2.21	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			28.8	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			27.9	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			20.8	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			20.2	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		119		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 150^{\circ}\text{C}$			10	W
		$t_p = 300\text{ }\mu\text{s}$				5	W
P_{GAV}	average gate power dissipation					0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 450\text{ A}$				150	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 0.45\text{ A}/\mu\text{s};$ $I_G = 0.45\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 150\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 150^{\circ}\text{C}$				1000	V/ μs
		$R_{GK} = \infty$ method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1.5	V
			$T_{VJ} = -40^{\circ}\text{C}$			1.6	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			150	mA
			$T_{VJ} = -40^{\circ}\text{C}$			200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}\text{C}$			0.2	V
I_{GD}	gate non-trigger current					10	mA
I_L	latching current	$t_p = 10\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			200	mA
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 150\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^{\circ}\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 20\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$			185		μs

Package E2-Pack				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				50	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		125	°C
Weight					176		g
M_D	mounting torque			3		6	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal		6,0			mm
$d_{Spb/Apb}$		terminal to backside		12,0			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4300			V
		t = 1 minute		3600			V



Part description

M = Module
 D = Diode
 M = Standard Rectifier
 A = (up to 1800V)
 360 = Current Rating [A]
 UC = 3~ Rectifier Bridge + Softstart-Thyristor
 1600 = Reverse Voltage [V]
 T = Thermistor \ Temperature sensor
 ED = E2-Pack

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA360UC1600TED	MDMA360UC1600TED	Box	6	524541

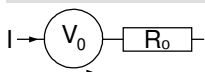
Temperature Sensor NTC

Symbol	Definition	Conditions	min.	typ.	max.	Unit
R_{25}	resistance	$T_{VJ} = 25^\circ$	4,85	5	5,15	kΩ
$B_{25/50}$	temperature coefficient			3375		K

Equivalent Circuits for Simulation

* on die level

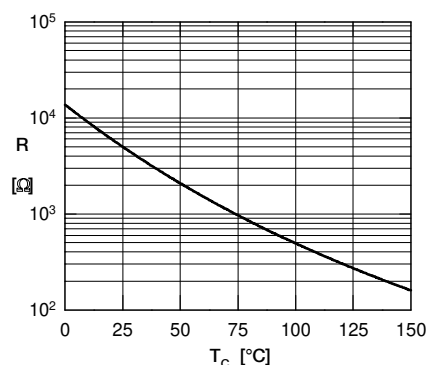
$T_{VJ} = 150^\circ\text{C}$

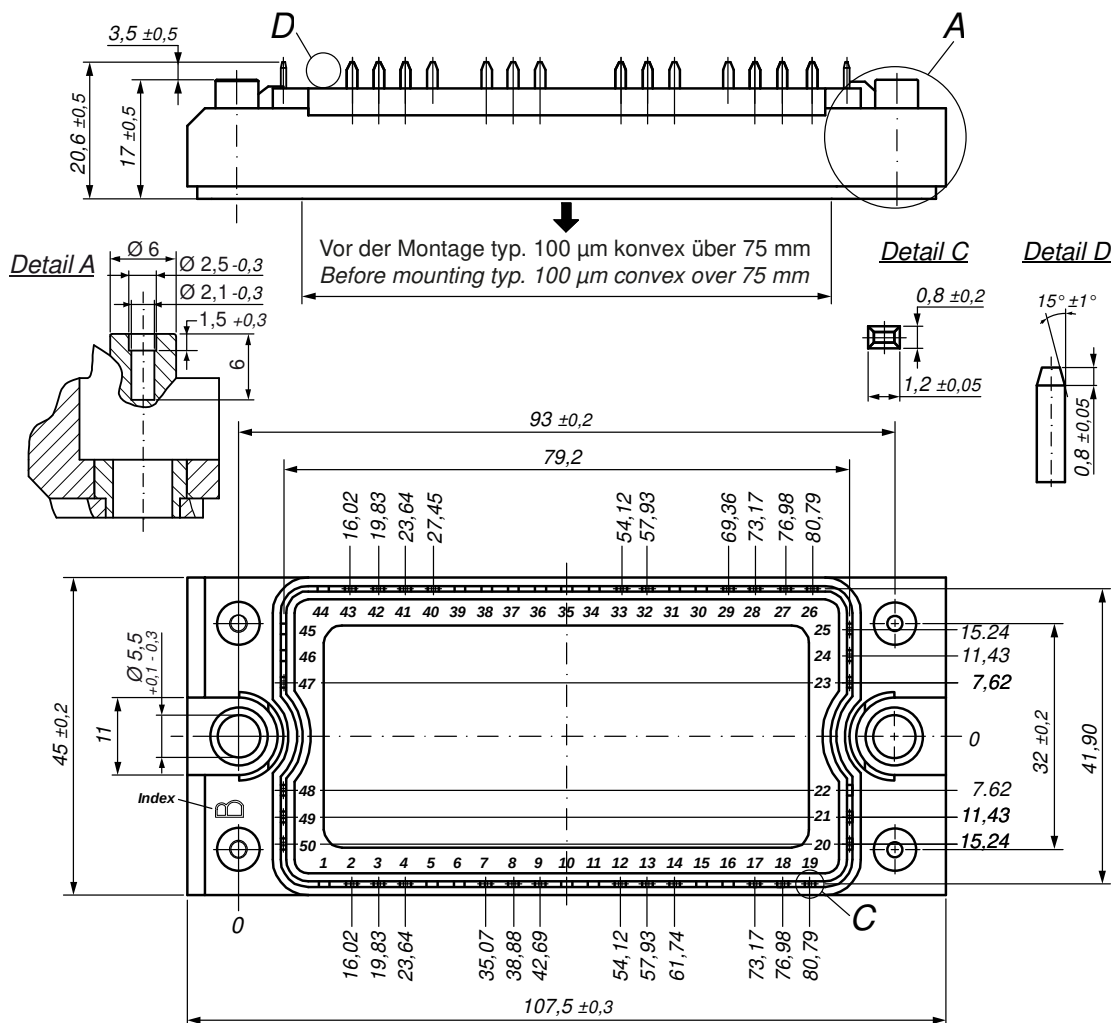


Rectifier

$V_{0\max}$ threshold voltage 0,82 V

$R_{0\max}$ slope resistance * 10,2 mΩ



Outlines E2-Pack

Bemerkung / Note:

- Nichttolerierete Maße nach / Measure without tolerances according DIN ISO 2768-T1-m

- PCB-Lochmuster / PCB hole pattern: **see pin position**

- Toleranz Pin-Position und PCB-Lochmuster / Tolerance of pin position and PCB hole pattern: $\oplus 0.1$

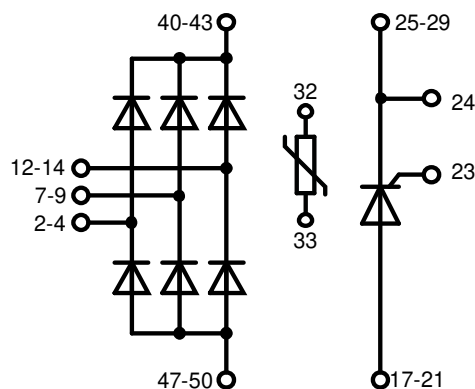
- Montageanleitung / Mounting instruction: www.ixys.com **Application note IXAN0024**

Detail A: PCB-Montage / Mounting on PCB

- Empfohlene, selbstschneidende Schraube / Recommended, self-tapping screw: **EJOT PT®** (Größe / size: **K25**)

- Max. Schraubenlänge / Max. screw length: **PCB-Dicke / thickness + 6 mm** (max. Lochtiefe / hole depth)

- Empfohlenes Drehmoment / Recommended mounting torque: **1.5 Nm**



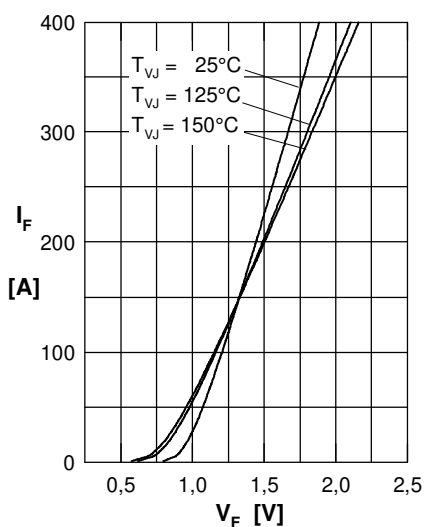
Rectifier


Fig. 1 Forward current versus voltage drop per diode

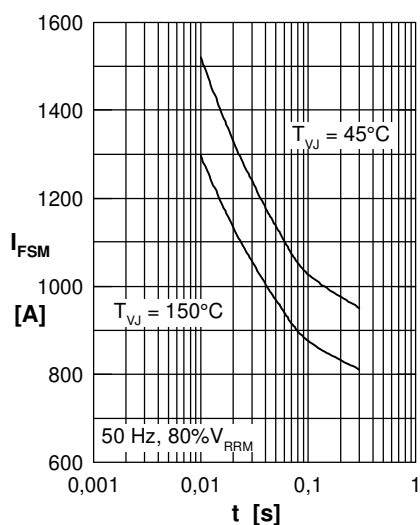


Fig. 2 Surge overload current vs. time per diode

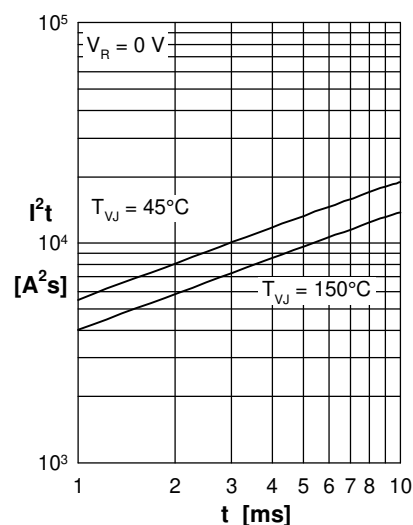
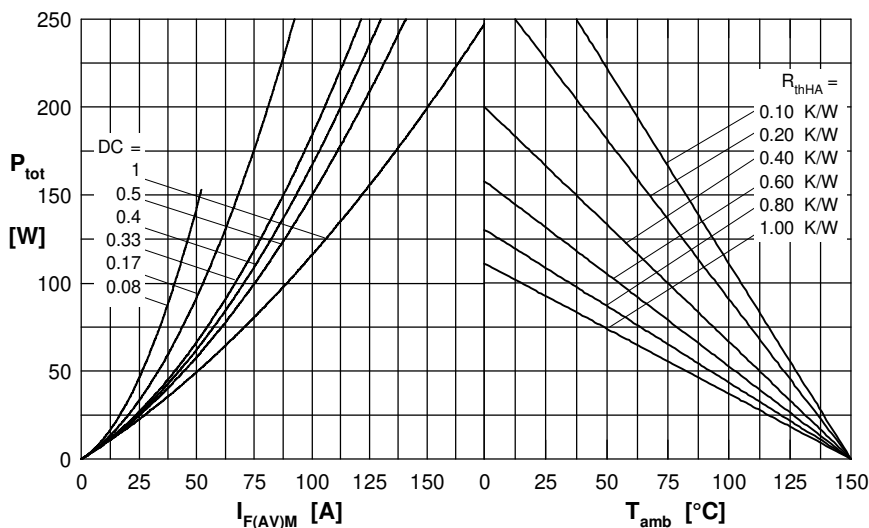

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

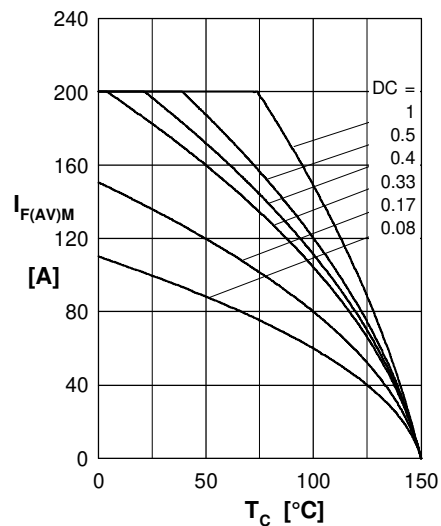


Fig. 5 Max. forward current vs. case temperature per diode

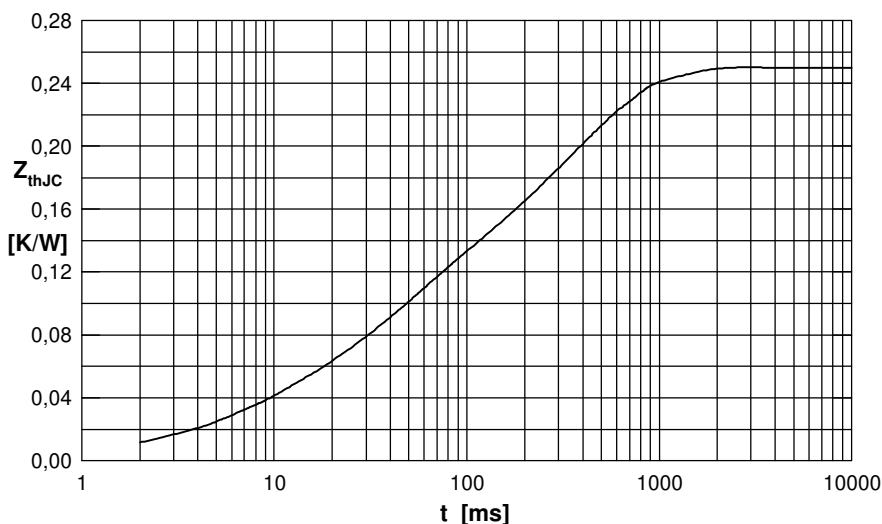


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.020	0.006
2	0.003	0.007
3	0.080	0.037
4	0.147	0.360

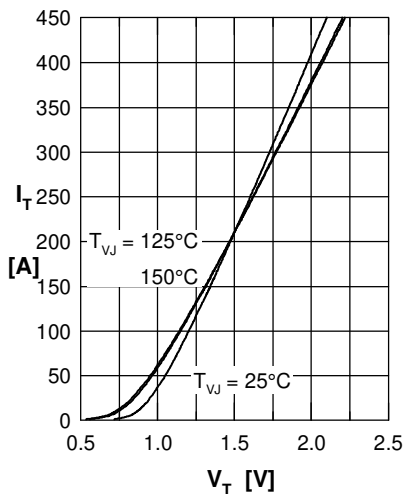
Softstart Thyristor


Fig. 1 Forward characteristics

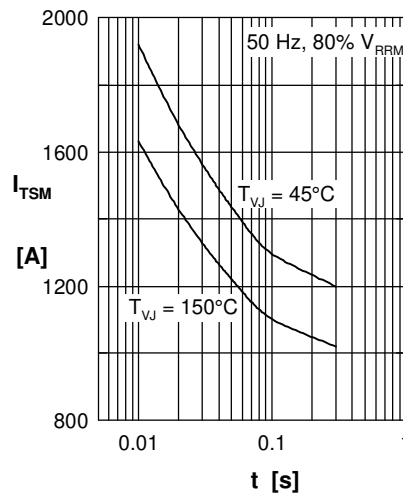
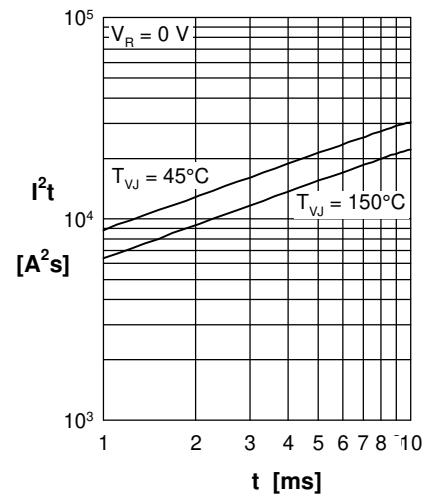
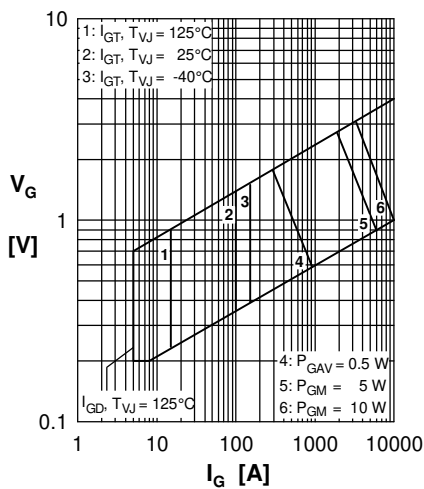

 Fig. 2 Surge overload current
 I_{TSM} : crest value, t : duration

 Fig. 3 I^2t versus time (1-10 s)


Fig. 4 Gate voltage & gate current

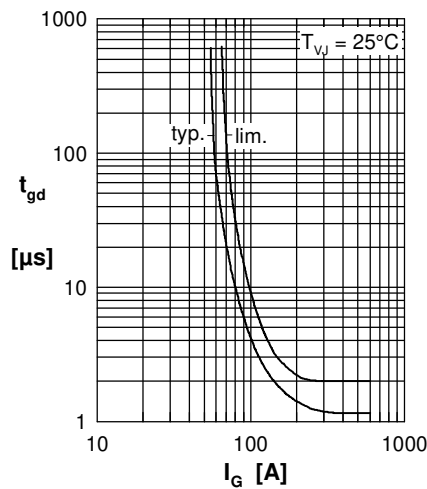
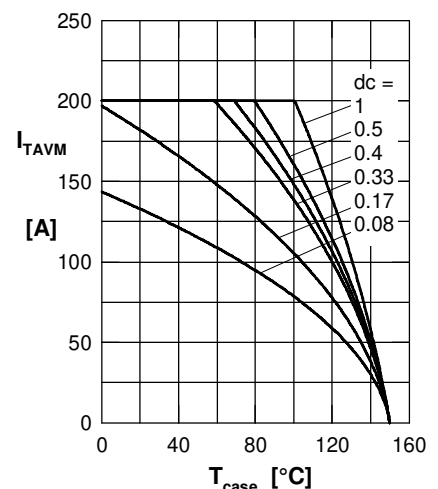

 Fig. 5 Gate controlled delay time t_{gd}


Fig. 6 Max. forward current at case temperature

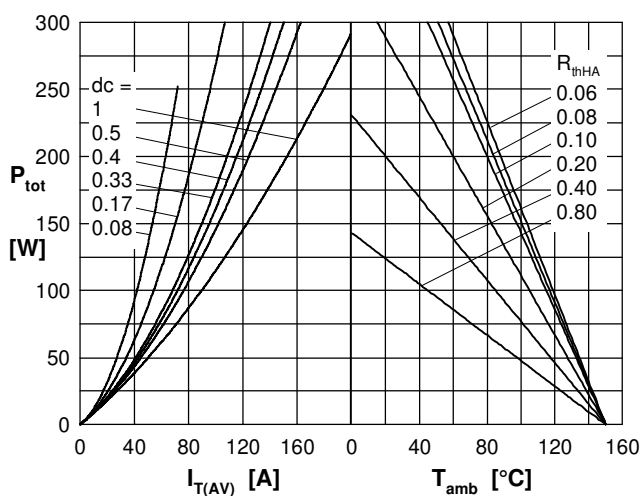
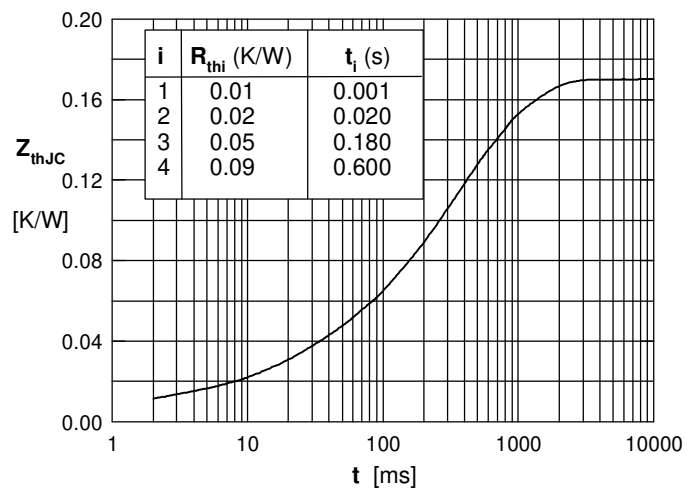

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance junction to case